

ABSTRACT

5       An object of the present invention is to provide a  
nitride semiconductor product which causes no time-  
dependent deterioration in reverse withstand voltage and  
maintains a satisfactory initial reverse withstand  
voltage.

10       The inventive nitride semiconductor product  
comprises an n-type layer, a light-emitting layer, and a  
p-type layer which are formed of a nitride semiconductor  
and sequentially stacked on a substrate in the above  
order,

15       the light-emitting layer having a quantum well  
structure in which a well layer is sandwiched by barrier  
layers having band gaps wider than the band gap of the  
well layer,

20       wherein each barrier layer comprises a barrier  
sublayer C which has been grown at a temperature higher  
than a growth temperature of the well layer, and a  
barrier sublayer E which has been grown at a temperature  
lower than a growth temperature of the barrier sublayer  
C, and the barrier sublayer C is disposed closer to the  
substrate with respect to the barrier sublayer E.